

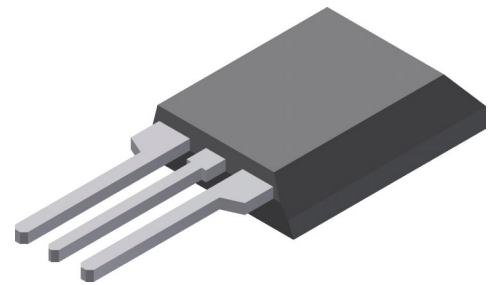
HiPerFRED

$$\begin{aligned} V_{RRM} &= 600\text{ V} \\ I_{FAV} &= 2 \times 10\text{ A} \\ t_{rr} &= 30\text{ ns} \end{aligned}$$

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Common Cathode

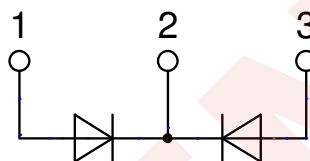
Part number

DSEC16-06AC



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: ISOPLUS220

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

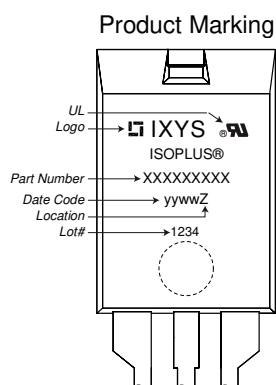
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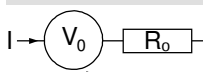
Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				600	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				600	V
I_R	reverse current, drain current	$V_R = 600\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			60	μA
		$V_R = 600\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			0,25	mA
V_F	forward voltage drop	$I_F = 10\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			2,10	V
		$I_F = 20\text{ A}$				2,32	V
		$I_F = 10\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$			1,42	V
		$I_F = 20\text{ A}$				1,68	V
I_{FAV}	average forward current	$T_C = 135^{\circ}\text{C}$ rectangular	$T_{VJ} = 175^{\circ}\text{C}$ d = 0.5			10	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^{\circ}\text{C}$		1,03	V
r_F	slope resistance					25,1	m Ω
R_{thJC}	thermal resistance junction to case					2,5	K/W
R_{thCH}	thermal resistance case to heatsink				0,5		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				60	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_R = 0\text{ V}$		$T_{VJ} = 45^{\circ}\text{C}$		50	A
C_J	junction capacitance	$V_R = 400\text{ V}$ f = 1 MHz		$T_{VJ} = 25^{\circ}\text{C}$		6	pF
I_{RM}	max. reverse recovery current	} $I_F = 10\text{ A}; V_R = 300\text{ V}$ -di _F /dt = 200 A/ μs		$T_{VJ} = 25^{\circ}\text{C}$		4	A
				$T_{VJ} = 100^{\circ}\text{C}$		6	A
t_{rr}	reverse recovery time			$T_{VJ} = 25^{\circ}\text{C}$		30	ns
				$T_{VJ} = 100^{\circ}\text{C}$		90	ns

Package ISOPLUS220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			35	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				2		g
F_c	mounting force with clip		20		60	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	1,0			mm
$d_{Spb/Apb}$		terminal to backside	3,0			mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEC16-06AC	DSEC16-06AC	Tube	50	505131

Similar Part	Package	Voltage class
DSEC16-06A	TO-220AB (3)	600

Equivalent Circuits for Simulation
** on die level*
 $T_{VJ} = 175^{\circ}\text{C}$

Fast Diode
 $V_{0\ max}$ threshold voltage

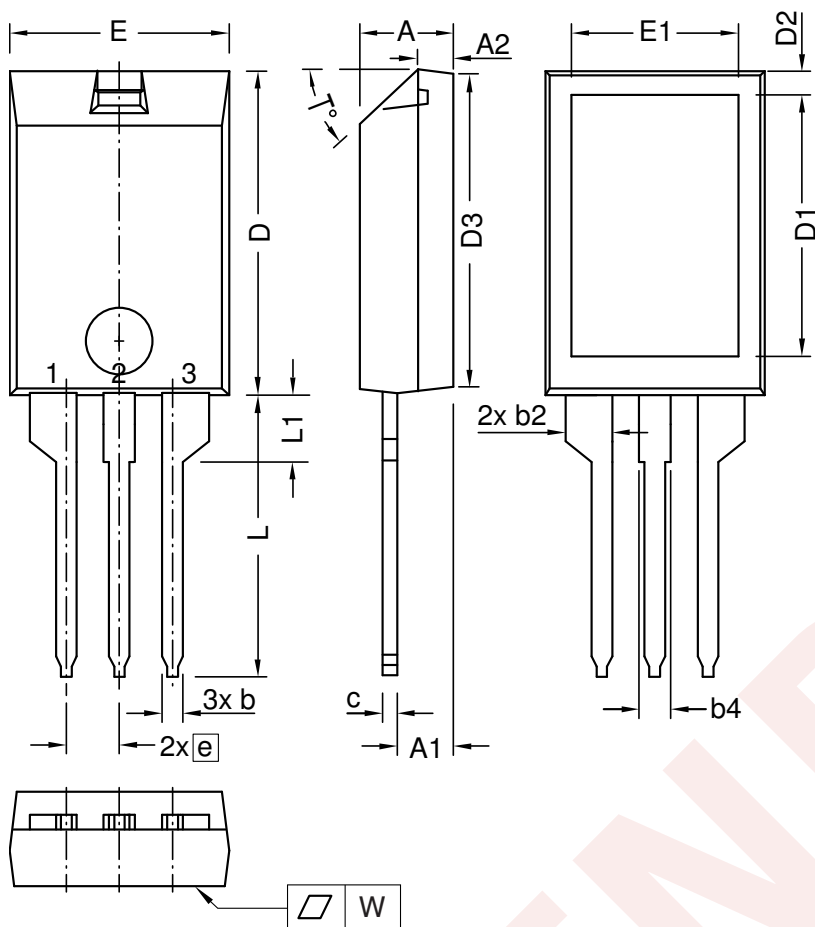
1,03

V

 $R_{0\ max}$ slope resistance *

22

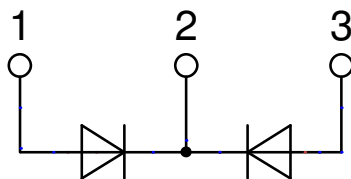
mΩ

Outlines ISOPLUS220


Dim.	Millimeters		Inches	
	min	max	min	max
A	4.00	5.00	0.157	0.197
A1	2.50	3.00	0.098	0.118
A2	1.60	1.80	0.063	0.071
b	0.90	1.30	0.035	0.051
b2	2.20	2.55	0.087	0.100
b4	1.25	1.65	0.049	0.065
c	0.70	1.00	0.028	0.039
D	15.00	16.00	0.591	0.630
D1	12.00	13.00	0.472	0.512
D2	1.10	1.50	0.043	0.059
D3	14.90	15.50	0.587	0.610
E	10.00	11.00	0.394	0.433
E1	7.50	8.50	0.295	0.335
e	2.54 BSC		0.100 BSC	
L	13.00	14.50	0.512	0.571
L1	3.00	3.50	0.118	0.138
T°	42.5	47.5		
W	-	0.1	-	0.004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite
 The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-273 gemäß JEDEC außer D und D1.
 This drawing will meet all dimensions requirement of JEDEC outline TO-273 except D and D1.



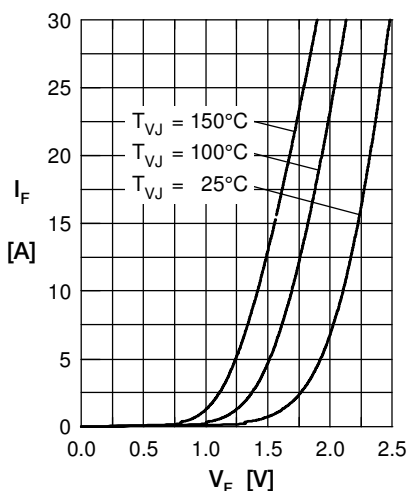
Fast Diode


Fig. 1 Forward current I_F versus V_F

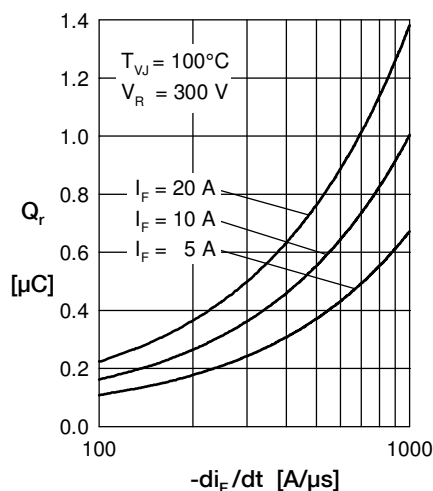


Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

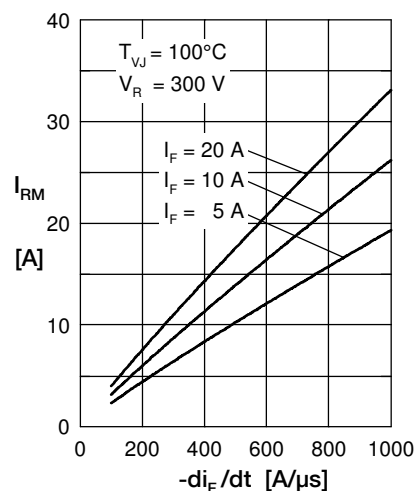


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

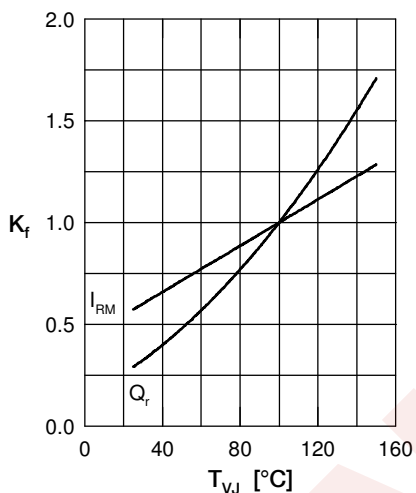


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

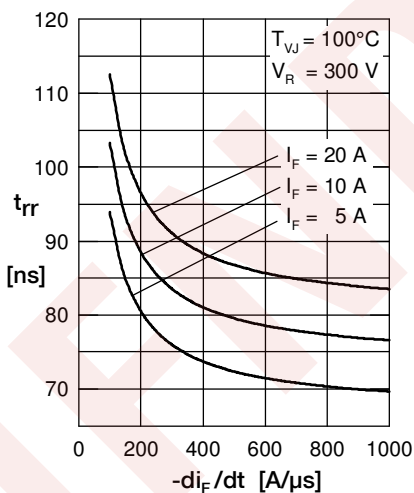


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

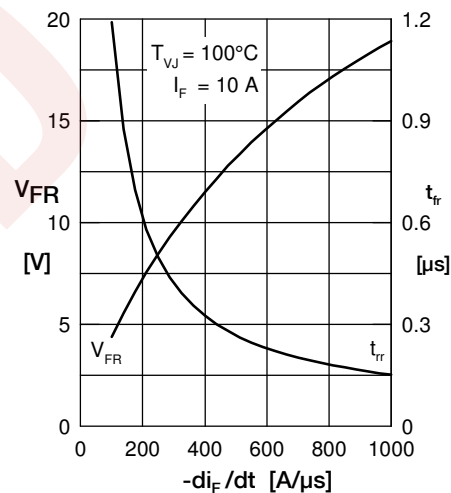


Fig. 6 Typ. peak forward voltage V_{FR} and t_{rr} versus di_F/dt

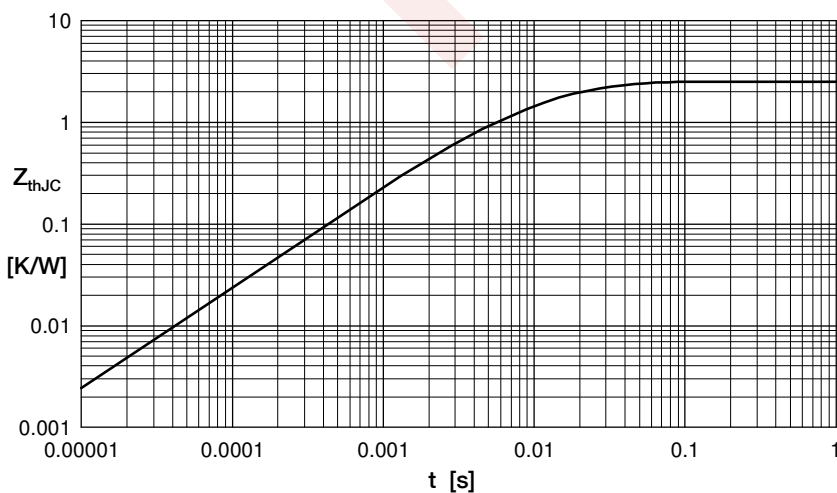


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	1.449	0.0052
2	0.5578	0.0003
3	0.4931	0.0169